

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (Withdrawn) A method for forming a layer of underfill adhesive on integrated circuits formed on a wafer, the integrated circuits having electrically conductive pads exposed on an active surface of the wafer, the method comprising:

forming solder bumps on the electrically conductive pads;

depositing underfill adhesive on the active surface of the wafer; and

curing the underfill adhesive.

2. (Withdrawn) The method as recited in claim 1 further comprising singulating the integrated circuits from the wafer wherein at least one of the singulated integrated circuits is a flip chip integrated circuit suitable for encapsulation in a flip chip package.

3. (Withdrawn) The method of claim 1, wherein the curing the underfill adhesive after depositing the underfill involves only partially curing the underfill adhesive without fully curing the underfill adhesive so that the underfill adhesive may be further cured when the associated solder bumps are reflowed to electrically connect the integrated circuits to substrates respectively.

4. (Withdrawn) The method of claim 1, wherein the underfill adhesive includes one or more of the following components: an epoxy resin, a hardener, a catalyst initiator, a coloring dye, and an inorganic filler.

5. (Withdrawn) The method of claim 1, wherein the underfill adhesive has a coefficient of thermal expansion substantially similar to a substrate or external device upon which the integrated circuits are mounted.

6. (Withdrawn) The method of claim 3, wherein the underfill adhesive is deposited on the active surface of the wafer at a pre-cured height such that the solder bumps are exposed through the underfill adhesive after the partial curing.

7. (Withdrawn) The method of claim 6, wherein the pre-cured height of the underfill adhesive applied to the wafer ranges from 140% to 90% of the height of the solder bumps.

8. (Withdrawn) The method as recited in claim 2, further comprising:
aligning selected ones of the solder bumps of the flip chip to corresponding bond pads included on a substrate upon which the flip chip is to be mounted;
mounting the flip chip integrated circuit on the substrate such that each of the selected solder bumps are in direct contact with the corresponding substrate bond pad; and
reflowing the solder bumps such that the flip chip bond pads are electrically connected to the corresponding substrate bond pads.

9. (Withdrawn) A method as recited in claim 1, wherein the underfill material is applied using stencil printing.

10. (Withdrawn) A method as recited in claim 1, wherein the underfill material is applied using one selected from the group consisting of screen printing, molding and spin-on deposition processes.

11. (Withdrawn) A method as recited in claim 1, wherein the underfill adhesive is selected from the group comprising: epoxies, poly-imides, silicone-polyimide copolymers.

12. (Withdrawn) The method of claim 1, wherein the underfill adhesive has a coefficient of thermal expansion in the range of approximately $20 \times 10^{-6}/K$ to approximately $30 \times 10^{-6}/K$ @ 25 °C.
13. (Withdrawn) The method of claim 1, wherein the underfill adhesive melts at between 120 to 140 degrees C and reacts at between 175 to 195 degrees C.
14. (Withdrawn) The method of claim 1, wherein the underfill adhesive has an elastic modulus in the range of 1 to 10 GPa.
15. (Withdrawn) The method of claim 1, further comprising forming a dam around the periphery of the wafer to prevent the underfill material deposited onto the active surface of the wafer from flowing off the wafer before the partial curing of the adhesive layer.
16. (Withdrawn) The method of claim 8, wherein a solder paste is provided on the bond pads of the substrate prior to mounting the flip chip.
17. (Withdrawn) The method of claim 8, wherein a fluxing material is provided on the substrate prior to mounting the flip chip.
18. (Withdrawn) The method of claim 1, wherein the underfill adhesive includes at least one of the following properties: a specific gravity ranging from 1.0 to 1.2; a solvent content ranging from 20% to 40%. a cure time of 20 to 30 minutes at 100 to 130 degrees C; and a filler content of 1% to 10% by weight.

19. (currently amended) An apparatus, comprising:

a flip chip integrated circuit having flip chip bond pads with solder bumps formed ~~thereon~~ directly an active surface of the flip chip; and

a substantially uniform layer of at least partially cured underfill adhesive formed on the active surface of the flip chip integrated circuit and around the solder bumps formed directly onto the active surface, the at least partially cured underfill adhesive being that is formed on the flip chip before the flip chip is mounted onto the substrate upon which the flip chip integrated circuit is intended to be mounted.

20. (original) The apparatus of claim 19, wherein the underfill adhesive includes one or more of the following components: an epoxy resin, a hardener, a catalyst initiator, a coloring dye, and an inorganic filler.

21. (previously amended) The apparatus of claim 19, wherein the underfill adhesive has a coefficient of thermal expansion substantially similar to that of the substrate upon which the flip chip integrated circuit is intended to be mounted.

22. (original) The apparatus of claim 19, wherein the underfill adhesive is deposited on the active surface of the flip chip integrated circuit at a pre-cured height such that the solder bumps are at least exposed through the underfill adhesive after the partial curing.

23. (original) The apparatus of claim 22, wherein the pre-cured height of the underfill adhesive applied to the wafer ranges from 140% to 90% of the height of the solder bumps.

24. (previously amended) The apparatus of claim 19, wherein the underfill adhesive layer is deposited on the active surface of the flip chip integrated circuit in wafer form before the flip chip integrated circuit is singulated from the wafer.

25. (previously amended) The apparatus of claim 19, wherein the underfill adhesive is selected from the group comprising: epoxies, poly-imides, silicone-polyimide copolymers.

26. (previously amended) The apparatus of claim 19, wherein the substrate has a plurality of contact pads, the contact pads configured to contact the solder bumps of the flip chip when the flip chip is mounted onto the substrate, the contact pads and the solder bumps forming joints electrically connecting the flip chip to the substrate.

27. (currently amended) The apparatus of claim 26, wherein the underfill adhesive material is fully cured ~~when the solder bumps of the flip chip and the contact pads of the substrate are reflowed.~~

28. (previously amended) The apparatus of claim 19, wherein the layer of underfill adhesive is substantially opaque thereby protecting the flip chip integrated circuit from photo induced leakage currents by blocking visible light.

29. (original) The apparatus of claim 19, wherein the underfill adhesive has a coefficient of thermal expansion in the range of approximately $20 \times 10^{-6}/K$ to approximately $30 \times 10^{-6}/K$ @ 25 °C.

30. (original) The apparatus of claim 19, wherein the underfill adhesive melts at between 120 to 140 degrees C and reacts at between 175 to 195 degrees C.

31. (original) The apparatus of claim 19, wherein the underfill adhesive has an elastic modulus in the range of 1 to 10 GPa.

32. (previously amended) The apparatus of claim 24, further comprising a dam around the periphery of the wafer to prevent the underfill material deposited onto the surface of the wafer from flowing off the wafer before the partial curing of the adhesive layer.

33. (currently amended) The apparatus of claim 26, wherein a solder paste is provided on the contact pads of the substrate ~~prior to mounting the flip chip~~.

34. (currently amended) The apparatus of claim 26, wherein a fluxing material is provided on the substrate ~~prior to mounting the flip chip~~.

35. (currently amended) An apparatus, comprising:

a semiconductor wafer having an active surface including a plurality of die formed thereon;

one or more bond pads formed on the plurality of die;

one or more solder bumps formed on the one or more bond pads respectively; and

a layer of at least partially cured underfill adhesive formed around the solder bumps on the active surface of the wafer.

30. (original) The apparatus of claim 19, wherein the underfill adhesive melts at between 120 to 140 degrees C and reacts at between 175 to 195 degrees C.

31. (original) The apparatus of claim 19, wherein the underfill adhesive has an elastic modulus in the range of 1 to 10 GPa.

32. (previously amended) The apparatus of claim 24, further comprising a dam around the periphery of the wafer to prevent the underfill material deposited onto the surface of the wafer from flowing off the wafer before the partial curing of the adhesive layer.

33. (currently amended) The apparatus of claim 26, wherein a solder paste is provided on the contact pads of the substrate ~~prior to mounting the flip chip~~.

34. (currently amended) The apparatus of claim 26, wherein a fluxing material is provided on the substrate ~~prior to mounting the flip chip~~.

35. (currently amended) An apparatus, comprising:

a semiconductor wafer having an active surface including a plurality of die formed thereon;

one or more bond pads formed on the plurality of die;

one or more solder bumps formed on the one or more bond pads respectively; and

a layer of at least partially cured underfill adhesive formed around the solder bumps on the active surface of the wafer.

36. (previously added) The apparatus of claim 35, wherein the underfill adhesive is deposited on the active surface of the wafer at a pre-cured height such that the solder bumps are at least exposed through the underfill adhesive after the partial curing.

37. (previously added) The apparatus of claim 36, wherein the pre-cured height of the underfill adhesive applied to the wafer ranges from 140% to 90% of the height of the solder bumps.

38. (previously added) The apparatus of claim 34, wherein the underfill adhesive is selected from the group comprising: epoxies, poly-imides, silicone-polyimide copolymers.

39. (previously added) A apparatus claim 34, wherein the layer of underfill adhesive is substantially opaque.

40. (previously added) The apparatus of claim 34, wherein the underfill adhesive has a coefficient of thermal expansion in the range of approximately $20 \times 10^{-6}/K$ to approximately $30 \times 10^{-6}/K$ @ 25 °C.

41. (previously added) The apparatus of claim 34, wherein the underfill adhesive melts at between 120 to 140 degrees C and reacts at between 175 to 195 degrees C.

42. (previously added) The apparatus of claim 34, wherein the underfill adhesive has an elastic modulus in the range of 1 to 10 GPa.

43. (previously added) The apparatus of claim 34, further comprising a dam around the periphery of the wafer to prevent the underfill material deposited onto the active surface of the wafer from flowing off the wafer before the partial curing of the adhesive layer.